

General Description

Description The WSD20L75DN uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

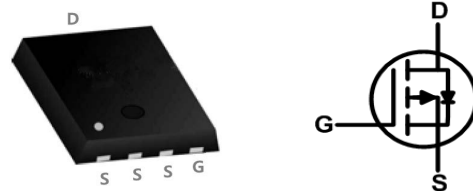
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
-20V	4.8m Ω	-75A

Applications

- Load switch
- Battery protection

DFN3X3-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-75	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-55	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-13	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
I_{DM}	Pulsed Drain Current ²	-200	A
EAS	Single Pulse Avalanche Energy ³	125	mJ
I_{AS}	Avalanche Current	-50	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	83	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	6.2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	55	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	20	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.5	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.0232	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-20A	---	4.8	6.0	mΩ
		V _{GS} =-2.5V, I _D =-20A	---	6.2	8	
		V _{GS} =-1.8V, I _D =-10A	---	8.0	10	
		V _{GS} =-1.5V, I _D =-8A	---	12	15.5	
		V _{GS} =-1.2V, I _D =-5A	---	17.6	19.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.6	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.6	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-20V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-20A	---	80	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	3	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-20A	---	55	75	nC
Q _{gs}	Gate-Source Charge		---	10	---	
Q _{gd}	Gate-Drain Charge		---	15	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3Ω, I _D =-20A, R _L =0.5Ω	---	18	---	ns
T _r	Rise Time		---	42	---	
T _{d(off)}	Turn-Off Delay Time		---	85	---	
T _f	Fall Time		---	23	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	3500	---	pF
C _{oss}	Output Capacitance		---	577	---	
C _{rss}	Reverse Transfer Capacitance		---	445	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =-10V, L=0.5mH, I _{AS} =-10A	100	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	-45	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	-90	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-10A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-10A, dI/dt=100A/μs, T _J =25°C	---	47	---	nS
Q _{rr}	Reverse Recovery Charge		---	53	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t_≤10sec.

2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3. The EAS data shows Max. rating. The test condition is V_{DD}=-10V, V_{GS}=-10V, L=0.1mH, I_{AS}=-10A

4. The power dissipation is limited by 150°C junction temperature

5. The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

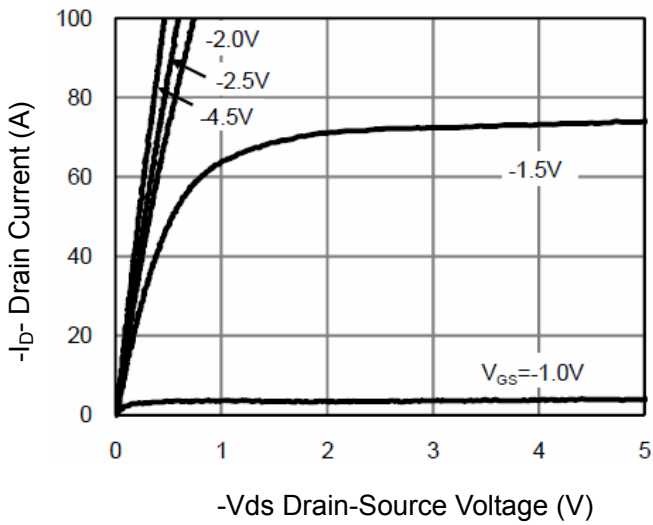


Figure 1 Output Characteristics

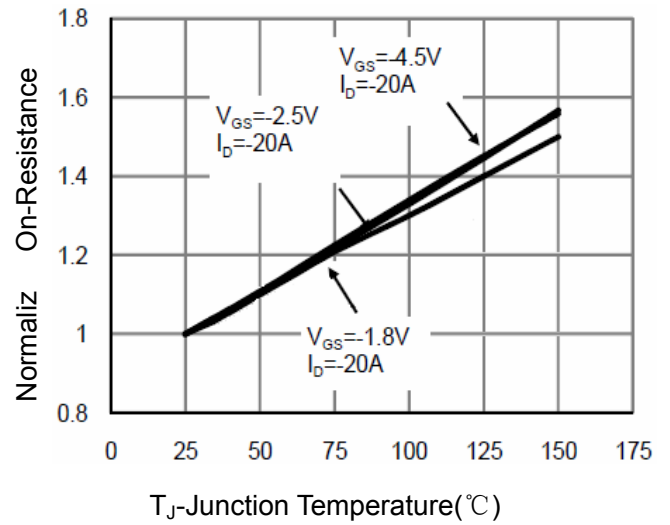


Figure 4 Rdson-Junction Temperature

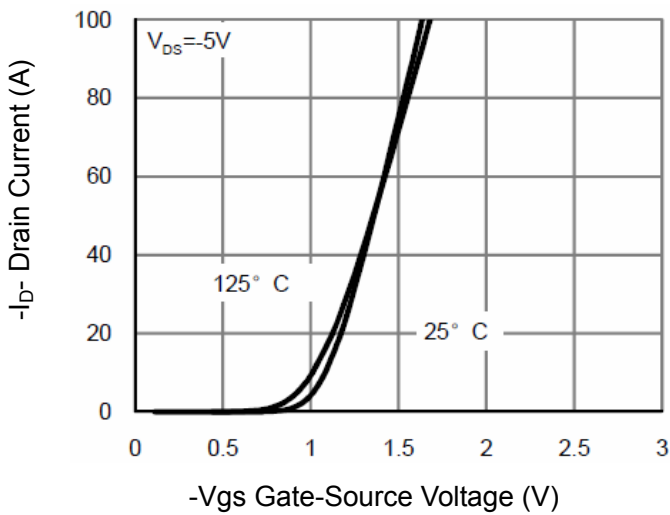


Figure 2 Transfer Characteristics

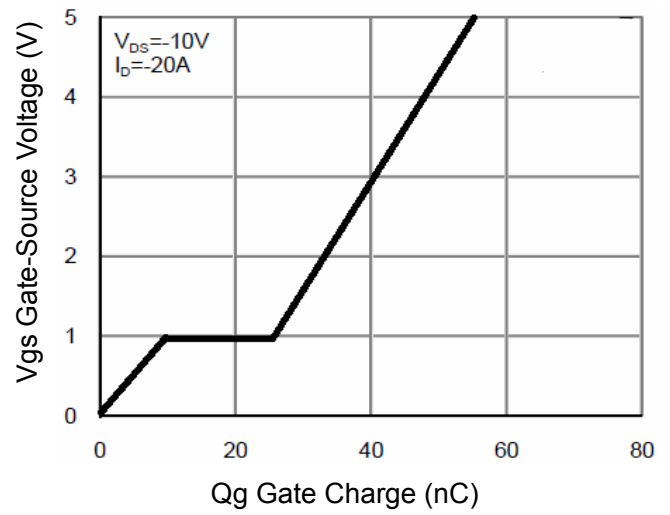


Figure 5 Gate Charge

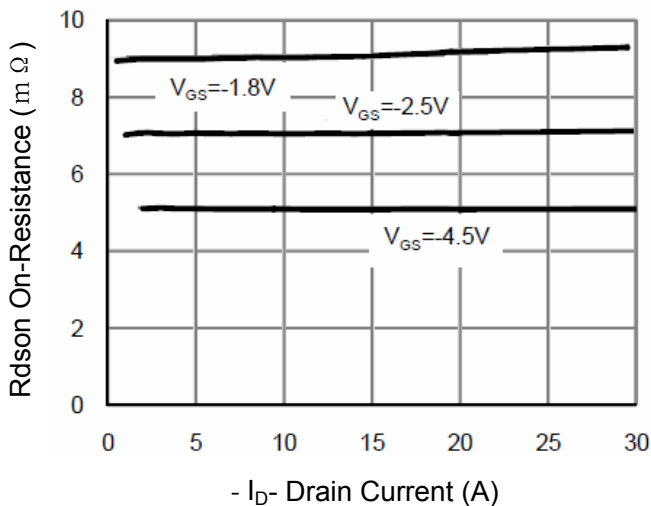


Figure 3 Rdson- Drain Current

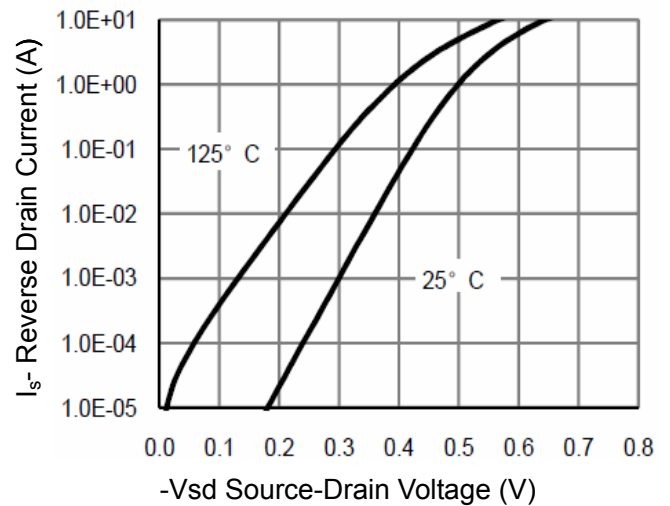


Figure 6 Source- Drain Diode Forward

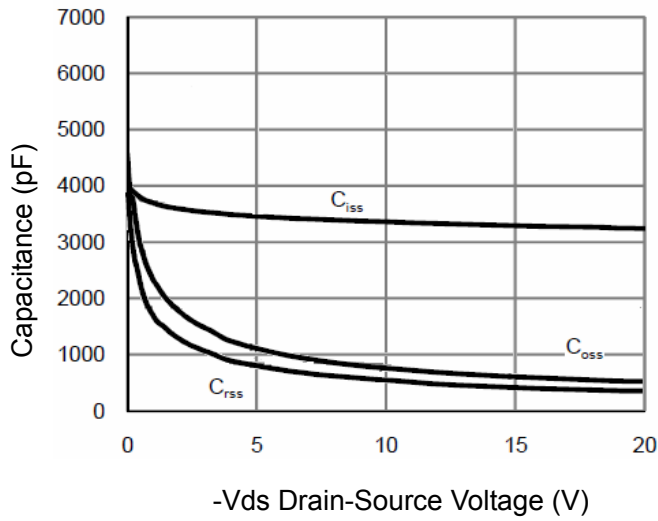


Figure 7 Capacitance vs Vds

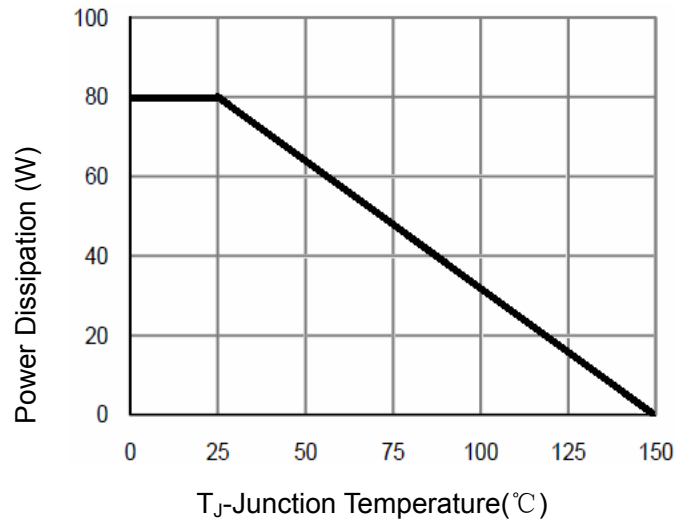


Figure 9 Power De-rating

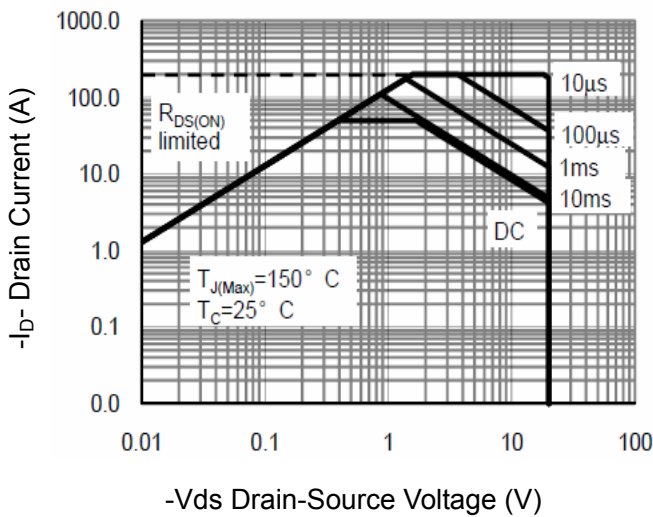


Figure 8 Safe Operation Area

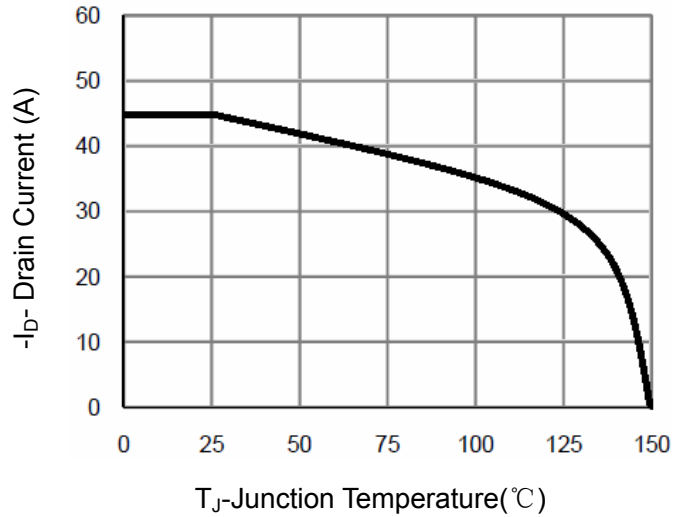


Figure 10 -Current De-rating

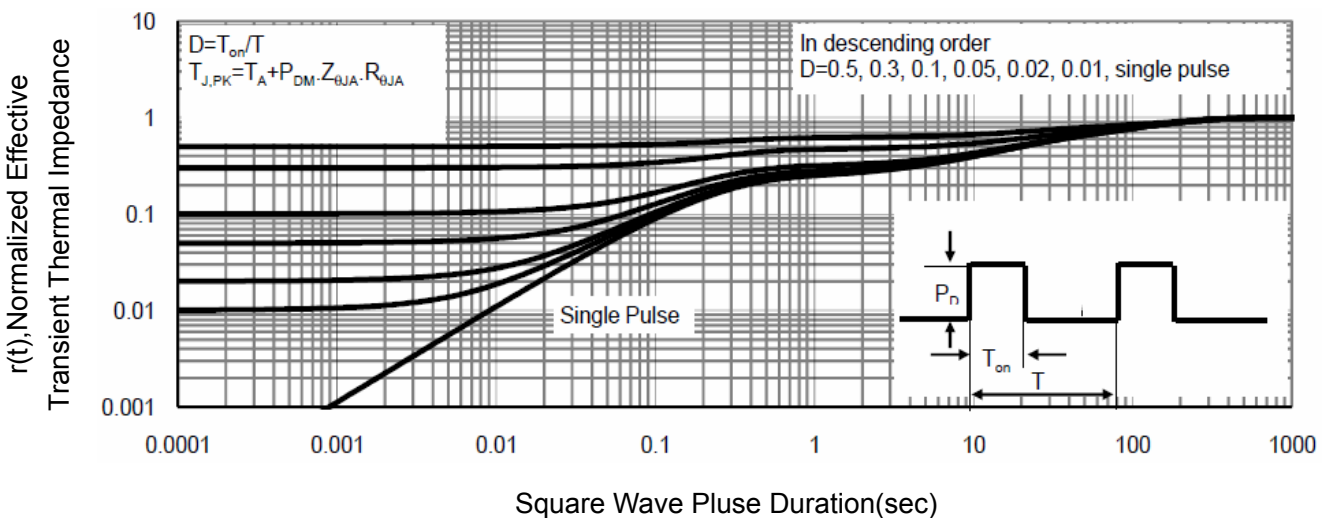


Figure 11 Normalized Maximum Transient Thermal Impedance



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